

ABSTRACT

A semiconductor device including a first active pattern and a second active pattern each extending along a first direction and arranged along a second direction intersecting the first direction each of the first and second active patterns including a central part, a first edge part, and a second edge part, a storage node pad on the first edge part of the first active pattern, and a bit-line node contact on the central part of the first active pattern, wherein a top surface of the bit-line node contact is located at a higher level than a top surface of the storage node pad may be provided.

FIG. 1